SiT3372 Advanced Information 10 MHz to 220 MHz Ultra-low Jitter Differential VCXO



Features

- Any frequency between 10 MHz and 220 MHz accurate to 6 decimal places
- Widest pull range options: ±25, ±50, ±80, ±100, ±150, ±200, ±400, ±800, ±1600, ±3200ppm
- 0.23 ps RMS phase jitter (Typ) over 12 kHz to 20 MHz bandwidth
- Wide temperature range support from -40°C to 85°C
 Contact SiTime for other temperature range options
- Industry-standard packages: 3.2x2.5, 7.0x5.0 mm Contact SiTIme for 5.0 x 3.2 mm package
- For frequencies 220 MHz to 720 MHz, refer to SiT3373 datasheet

Applications

- Remote Radio Head (RRH), Cable Modem Termination System (CMTS), Video, Broadcasting System, Audio, Industrial Sensors
- SATA, SAS, 10GB Ethernet, Fibre Channel, PCI-Express







Electrical Characteristics

All Min and Max limits in the Electrical Characteristics tables are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage

Table 1. Electrical Characteristics - Common to LVPECL, LVDS and HCSL

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition					
			F	requency Ra	inge						
Output Frequency Range	f	10	_	220	MHz	Accurate to 6 decimal places					
	ı	I.	Fr	equency Sta	bility						
		-15	_	+15	ppm						
Francisco Ctability	□ otob	-25	-	+25	ppm	Inclusive of initial tolerance, operating temperature, rated power supply voltage, load variations, and first year aging at 25°C					
Frequency Stability	F_stab	-30	-	+30	ppm	condition					
		-50	-	+50	ppm						
	Temperature Range										
Operating Temperature Range	T use	-20	-	+70	°C	Extended Commercial					
Operating reinperature Kange	1_use	-40	-	+85	°C	Industrial. Contact SiTime for other temperature range options.					
				Supply Volta	age						
	Vdd	2.97	3.3	3.63	V						
		2.7	3.0	3.3	V						
Supply Voltage		2.52	2.8	3.08	V						
		2.25	2.5	2.75	V						
	ı	I.	Voltage	Control Cha	racteristics	1					
Pull Range	PR		±80, ±100, ±		ppm	See the last page for Absolute Pull Range, APR Table. Contact SiTime for custom pull range options.					
Upper Control Voltage	VC_U	90%	-	-	Vdd	Voltage at which maximum frequency deviation is guaranteed					
Lower Control Voltage	VC_L	-	-	10%	Vdd	Voltage at which minimum frequency deviation is guaranteed					
Control Voltage Input Impedance	VC_z	-	10	_	ΜΩ						
Control Voltage Input Bandwidth	V_c	-	10	1	kHz	Contact SiTime for other input bandwidth options					
Pull Range Linearity	Lin	i	1	TBD	%						
Frequency Change Polarity	-		Positive Slop	е	_						
			Inp	ut Characte	ristics						
Input Voltage High	VIH	70%	-	-	Vdd	Pin 2, OE					
Input Voltage Low	VIL	-	-	30%	Vdd	Pin 2, OE					
Input Pull-up Impedance	Z_in	-	100	-	kΩ	Pin 2, OE logic high or logic low					



Table 2. Electrical Characteristics - Common to LVPECL, LVDS and HCSL (Cont'd)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition			
Output Characteristics									
Duty Cycle	DC	45	-	55	%				
	Startup and OE Timing								
Start-up Time T_start - 5 ms Measured from the time Vdd reaches its rated mi			Measured from the time Vdd reaches its rated minimum value.						
OE Enable/Disable Time	T_oe	ı		515	ns	f = 212.5 MHz - For other frequencies, T_oe = 500ns + 3 period			

Table 3. Electrical Characteristics - LVPECL Specific

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition		
			Cı	ırrent Co	nsump	tion		
Current Consumption	ldd	_	-	84	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V		
OE Disable Supply Current	I_OE	-	-	55	mA	OE = Low		
Output Disable Leakage Current	I_leak	-	0.15	_	μΑ	OE = Low		
Maximum Output Current	I_driver	-	-	30	mA	Maximum average current drawn from OUT+ or OUT-		
Output Characteristics								
Output High Voltage	VOH	Vdd-1.1	-	Vdd-0.7	V	See Figure 2		
Output Low Voltage	VOL	Vdd-1.9	_	Vdd-1.5	V	See Figure 2		
Output Differential Voltage Swing	V_Swing	1.2	1.6	2.0	V	See Figure 3		
Rise/Fall Time	Tr, Tf	-	250	_	ps	20% to 80%, see Figure 2		
				Jitt	ter			
RMS Period Jitter ^[1]	T_jitt	_	1	2	ps	f = 156.25 MHz, VDD = 3.3V or 2.5V		
	T_phj	_	0.23	_	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds		
RMS Phase Jitter (random)		-	0.1	-	ps	f = 156.25 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, all Vdds		

Notes:

Table 4. Electrical Characteristics - LVDS Specific

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition		
			Cı	irrent Co	nsump	tion		
Current Consumption	ldd	-	_	76	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V		
OE Disable Supply Current	I_OE	-	_	55	mA	OE = Low		
Output Disable Leakage Current	I_leak	-	0.15	_	μΑ	OE = Low		
Output Characteristics								
Differential Output Voltage	VOD	250	_	450	mV	See Figure 4		
VOD Magnitude Change	ΔVOD	-	_	50	mV	See Figure 4		
Offset Voltage	VOS	1.125	_	1.375	V	See Figure 4		
VOS Magnitude Change	ΔVOS	-	_	50	mV	See Figure 4		
Rise/Fall Time	Tr, Tf	ı	340	-	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 4		
				Jit	ter			
RMS Period Jitter ^[2]	T_jitt	_	1	2	ps	f = 156.25 MHz, VDD = 3.3V or 2.5V		
RMS Phase Jitter (random)	T_phj	-	0.23	-	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds		
		-	0.1	_	ps	f = 156.25 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, all Vdds		

Notes:

2. Measured according to JESD65B

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^{1.} Measured according to JESD65B

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Table 5. Electrical Characteristics – HCSL Specific

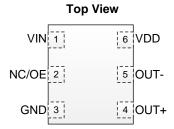
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition		
			Cu	rrent Co	nsumpt	ion		
Current Consumption	ldd	-	_	84	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V		
OE Disable Supply Current	I_OE	ı	-	55	mA	OE = Low		
Output Disable Leakage Current	I_leak	1	0.15	-	μΑ	OE = Low		
Output Characteristics								
Output High Voltage	VOH	0.6	-	0.8	V	See Figure 2		
Output Low Voltage	VOL	-0.05	-	0.05	V	See Figure 2		
Output Differential Voltage Swing	V_Swing	1	1.4	1.8	V	See Figure 3		
Rise/Fall Time	Tr, Tf	ı	350	-	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 2		
				Jitt	ter			
RMS Period Jitter ^[3]	T_jitt	-	1	2	ps	f = 156.25 MHz, VDD = 3.3V or 2.5V		
		-	0.23	_	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds		
RMS Phase Jitter (random)	T_phj	-	0.1	-	ps	f = 156.25 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, all Vdds		

Notes:

3. Measured according to JESD65B

Table 6. Pin Description

Pin	Symbol	Functionality					
1	VIN	Input	Control Voltage				
2	NC/OE	No Connect (NC)	No Connect: Leave it floating or connect to GND for better heat dissipation				
2	NC/OE	Output Enable (OE)	H ^[4] : specified frequency output L: output is high impedance. Only output driver is disabled				
3	GND	Power	VDD Power Supply Ground				
4	OUT+	Output	Oscillator output				
5	OUT-	Output	Complementary oscillator output				
6	VDD	Power	Power supply voltage ^[5]				



- 4. In OE mode, a pull-up resistor of 10 $k\Omega$ or less is recommended if pin 1 is not externally driven.
- 5. A capacitor of value 0.1 μF or higher between Vdd and GND is required. An Additional 10 pF between Vdd and GND is required for the best phase jitter performance

Figure 1. Pin Assignments

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Table 7. Absolute Maximum

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
VDD	-0.5	4	V
Electrostatic Discharge (HBM)	-	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	-	260	°C

Table 8. Thermal Consideration^[6]

Package	θJA, 4 Layer Board (°C/W)	θJC, Bottom (°C/W)
3225, 6-pin	TBD	TBD
7050, 6-pin	TBD	TBD

Notes:

Table 9. Maximum Operating Junction Temperature^[7]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
70°C	80
85°C	95

Notes:

Table 10. Environmental Compliance

Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method 2002
Mechanical Vibration	MIL-STD-883F, Method 2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method 2003
Moisture Sensitivity Level	MSL1 @ 260°C

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^{6.} Refer to JESD51 for θ JA and θ JC definitions, and reference layout used to determine the θ JA and θ JC values in the above table.

^{7.} Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.



Waveform Diagrams

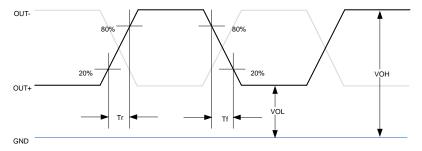


Figure 2. LVPECL/HCSL Voltage Levels per Differential Pin (OUT+/OUT-)

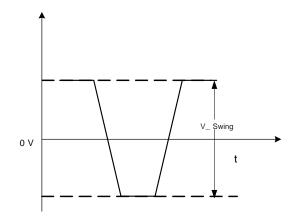


Figure 3. LVPECL/HCSL Voltage Levels across Differential Pair

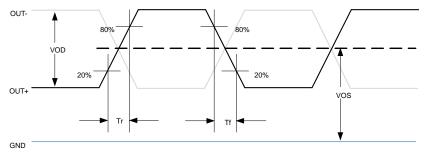


Figure 4. LVDS Voltage Levels per Differential Pin (OUT+/OUT-)

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Termination Diagrams

LVPECL:

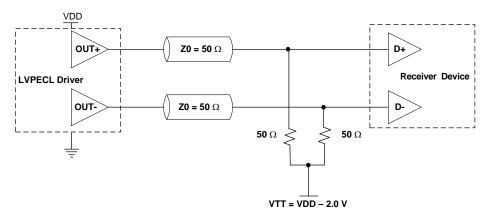


Figure 5. LVPECL Typical Termination

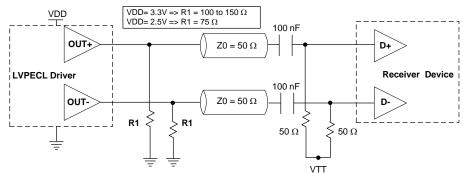


Figure 6. LVPECL AC Coupled Termination

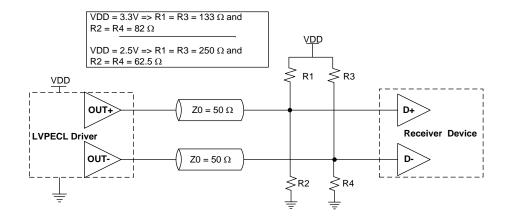


Figure 7. LVPECL with Thevenin Typical Termination

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Termination Diagrams (Continued)

LVDS:

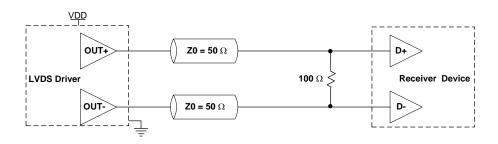


Figure 8. LVDS Single Termination (Load Terminated)

HCSL:

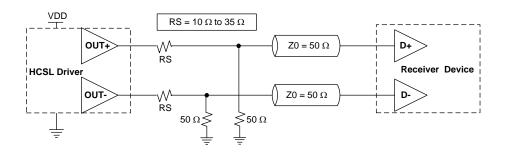
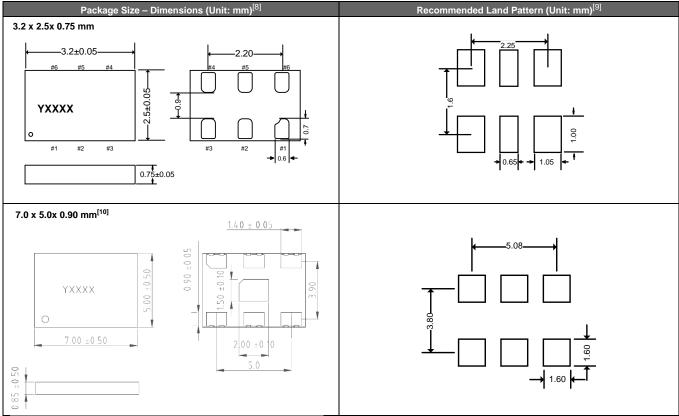


Figure 9. HCSL Typical Termination

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Dimensions and Patterns



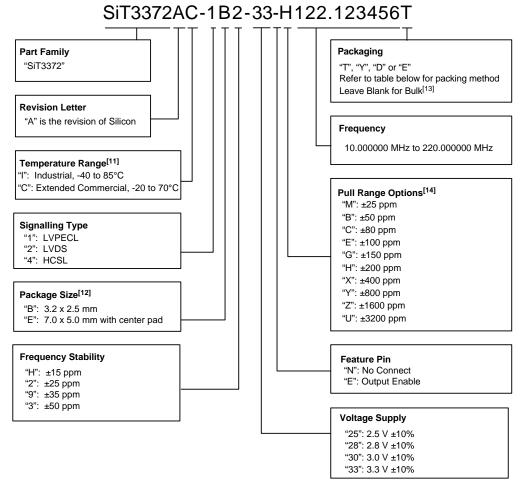
Notes:

- 8. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
- 9. A capacitor of value 0.1 μF or higher between Vdd and GND is required.
- 10. The center pad has no electrical function. Soldering down the center pad to the GND is recommended for best thermal dissipation, but is optional.

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Ordering Information



Notes:

- 11. Contact SiTime for higher temperature options
- 12. Contact SiTime for 5.0 x 3.2 package
- 13. Bulk is available for sampling only
- 14. Contact SiTime for custom pull range options

Table 11. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	8 mm T&R (3ku)	8 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	16 mm T&R (3ku)	16 mm T&R (1ku)
7.0 x 5.0	_	_	_	_	Т	Υ
3.2 x 2.5	D	E	Т	Υ		_

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Table 12. APR Table

Absolute pull range (APR) = Nominal pull range (PR) - frequency stability (F_stab)

		Frequenc	y Stability	
Nominal Pull Range	± 15	± 25	± 35	±50
		APR	(ppm)	
± 25	± 5	_	ı	_
± 50	± 30	± 20	± 10	_
± 80	± 60	± 50	± 40	± 25
± 100	± 80	± 70	± 60	± 45
± 150	± 130	± 120	± 110	± 95
± 200	± 180	± 170	± 160	± 145
± 400	± 380	± 370	± 360	± 345
± 800	± 780	± 770	± 760	± 745
± 1600	± 1580	± 1570	± 1560	± 1545
± 3200	± 3180	± 3170	± 3160	± 3145

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